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Title: An Energy-Efficient Tensile-

Strained Ge/InGaAs TFET 7T SRAM Cell Architecture for Ultralow-Voltage Applications

Jheng-Sin Liu

Publication: Electron Devices, IEEE

Transactions on

Publisher: IEEE

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Title: Performance Evaluation of Novel

Strain-Engineered Ge-InGaAs Heterojunction Tunnel Field-

Effect Transistors

Author: Jheng-Sin Liu

Publication: Electron Devices, IEEE

Transactions on

Publisher: IEEE

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Tailoring the Valence Band Offset of Al2O3 on Epitaxial GaAs1-ySby with Tunable Antimony Composition

Author: Jheng-Sin Liu, Michael Clavel,

Mantu K. Hudait

Publication: Applied Materials

Publisher: American Chemical Society

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Heterointerface Engineering of Broken-Gap InAs/GaSb

Multilayer Structures

Author: Jheng-Sin Liu, Yan Zhu, Patrick

S. Goley, et al

Publication: Applied Materials

Publisher: American Chemical Society

Date: Feb 1, 2015

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